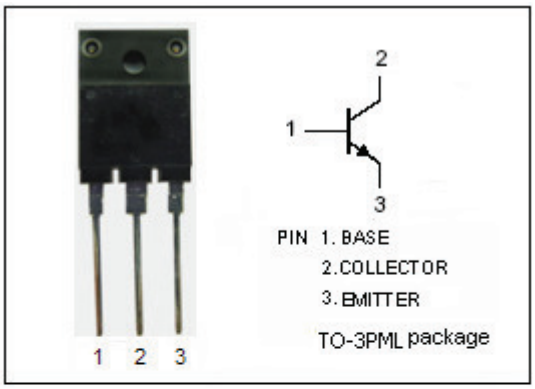
isc Silicon NPN Power Transistor 2SC2987A



DESCRIPTION

·Collector-Emitter Breakdown Voltage-

: $V_{(BR)CEO}$= 160V(Min)

·Good Linearity of h_{FE}

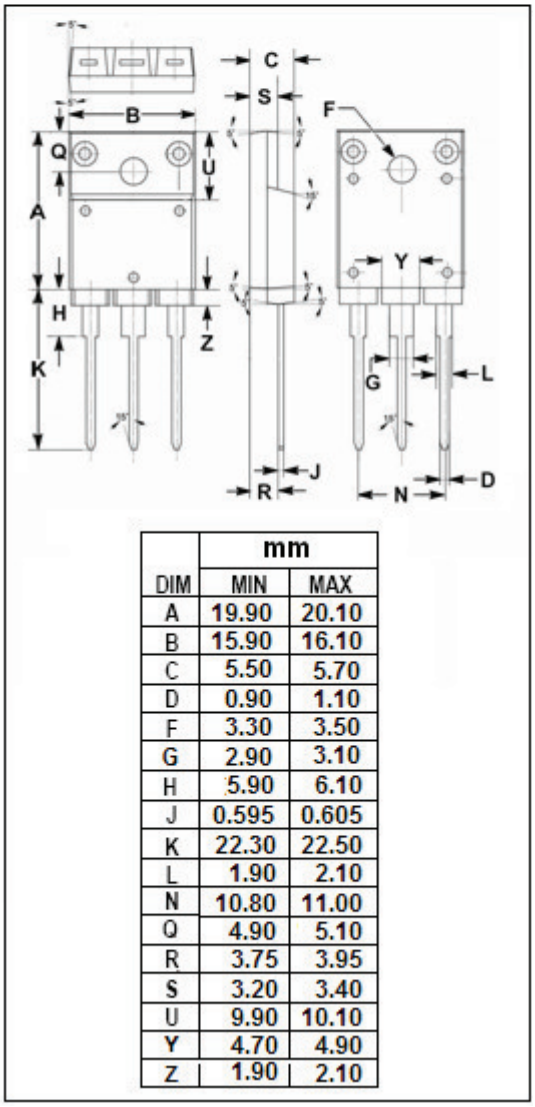
·Complement to Type 2SA1227A

APPLICATIONS

·For audio frequency power amplifier applications.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	160	V
V_{CEO}	Collector-Emitter Voltage	160	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current-Continuous	12	A
I_{CP}	Collector Current-Pulse	20	A
P_C	Collector Power Dissipation @ T_C=25℃	80	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃



DIM	mm MIN	MAX
A	19.90	20.10
B	15.90	16.10
C	5.50	5.70
D	0.90	1.10
F	3.30	3.50
G	2.90	3.10
H	5.90	6.10
J	0.595	0.605
K	22.30	22.50
L	1.90	2.10
N	10.80	11.00
Q	4.90	5.10
R	3.75	3.95
S	3.20	3.40
U	9.90	10.10
Y	4.70	4.90
Z	1.90	2.10

isc Silicon NPN Power Transistor 2SC2987A

ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= 5.0A; I_B= 0.5A			1.5	V
$V_{BE(sat)}$	Base -Emitter Saturation Voltage	I_C= 5.0A; I_B= 0.5A			2.0	V
I_{CBO}	Collector Cutoff Current	V_{CB}= 140V; I_E= 0			50	μ A
I_{EBO}	Emitter Cutoff Current	V_{EB}= 3V; I_C= 0			50	μ A
h_{FE-1}	DC Current Gain	I_C= 2A; V_{CE}= 5V	60		320	
h_{FE-2}	DC Current Gain	I_C= 5A; V_{CE}= 5V	40			
C_{OB}	Output Capacitance	I_E= 0; V_{CB}= 10V; f_{test}= 1.0MHz		190		pF
f_T	Current-Gain—Bandwidth Product	I_C= 1A; V_{CE}= 5V		50		MHz

◆ **h_{FE-1} Classifications**

R	Q	P
60-120	100-200	160-320